



2N7002KFN3

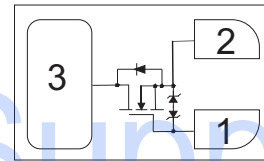
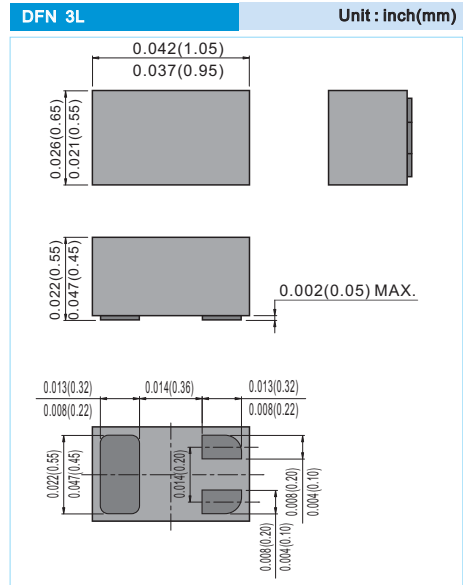
60V N-Channel Enhancement Mode MOSFET - ESD Protected

FEATURES

- $R_{DS(ON)}, V_{GS}@10V, I_{DS}@500mA=3\Omega$
- $R_{DS(ON)}, V_{GS}@4.5V, I_{DS}@200mA=4\Omega$
- Advanced Trench Process Technology
- High Density Cell Design For Ultra Low On-Resistance
- Very Low Leakage Current In Off Condition
- Specially Designed for Battery Operated Systems, Solid-State Relays Drivers : Relays, Displays, Lamps, Solenoids, Memories, etc.
- ESD Protected 2KV HBM
- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

- Case: DFN 3L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Marking : AU



Datasheet.Support

Maximum RATINGS and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	Symbol	Limit	Units
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	115	mA
Pulsed Drain Current ¹⁾	I _{DM}	800	mA
Maximum Power Dissipation	P _D	T _A =25°C 200 T _A =75°C 150	mW
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to + 150	°C
Junction-to Ambient Thermal Resistance(PCB mounted) ²	R _{θJA}	883	°C/W

Note: 1. Maximum DC current limited by the package
2. Surface mounted on FR4 board, t < 5 sec

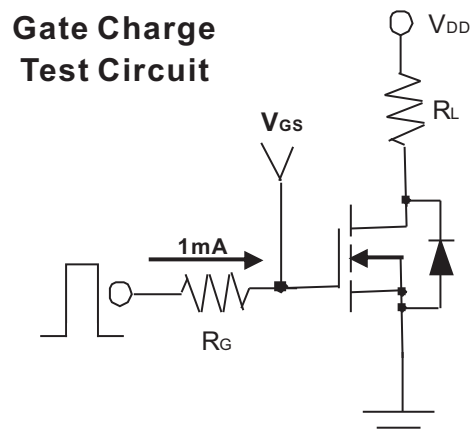
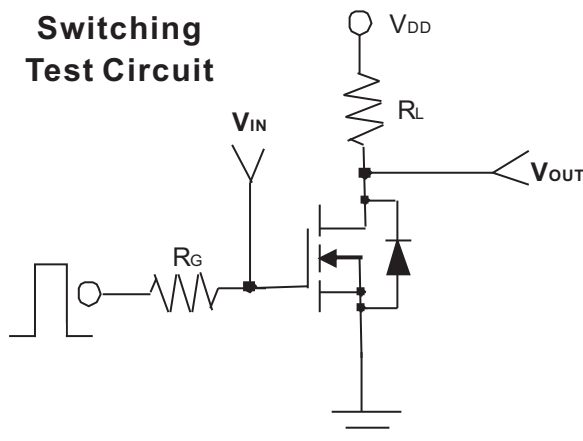
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ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=10\mu A$	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=200mA$	-	-	4.0	Ω
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=500mA$	-	-	3.0	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate Body Leakage	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 10	μA
Forward Transconductance	g_{fs}	$V_{DS}=15V, I_D=250mA$	100	-	-	mS
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=200mA$ $V_{GS}=4.5V$	-	-	0.8	nC
Turn-On Delay Time	t_{on}	$V_{DD}=30V, R_L=150\Omega$ $I_D=200mA, V_{GEN}=10V$ $R_G=10\Omega$	-	-	20	ns
Turn-Off Delay Time	t_{off}		-	-	40	
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V$ $f=1.0MHz$	-	-	35	μF
Output Capacitance	C_{oss}		-	-	10	
Reverse Transfer Capacitance	C_{rss}		-	-	5	
Source-Drain Diode						
Diode Forward Voltage	V_{SD}	$I_S=200mA, V_{GS}=0V$	-	0.82	1.3	V
Continuous Diode Forward Current	I_S	-	-	-	115	mA
Pulsed Diode Forward Current	I_{SM}	-	-	-	800	mA





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Typical Characteristics Curves ($T_J=25^\circ\text{C}$, unless otherwise noted)

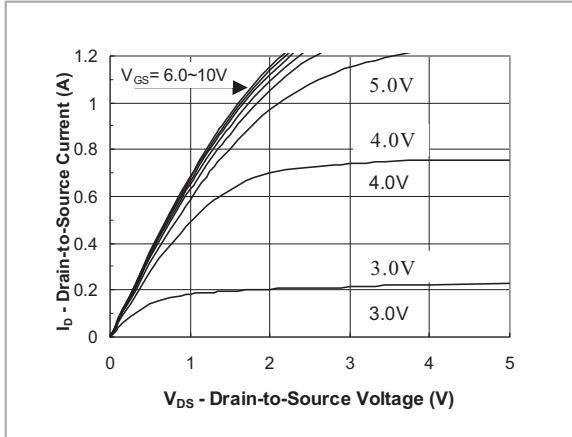


FIG.1- Output Characteristic

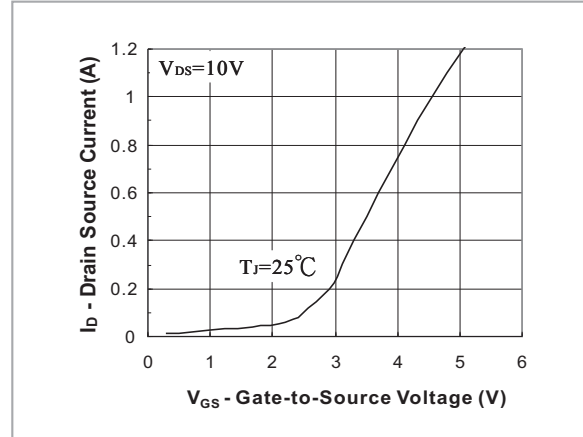


FIG.2- Transfer Characteristic

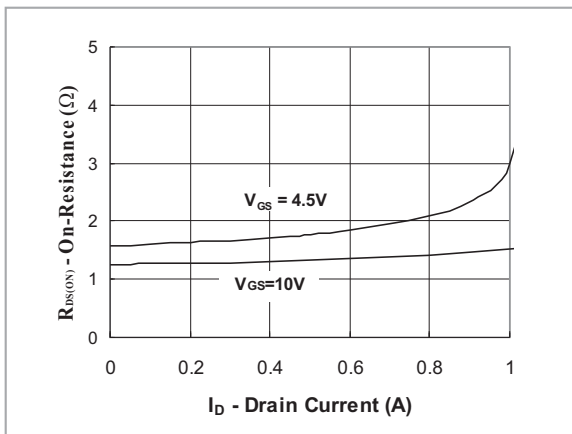


FIG.3- On Resistance vs Drain Current

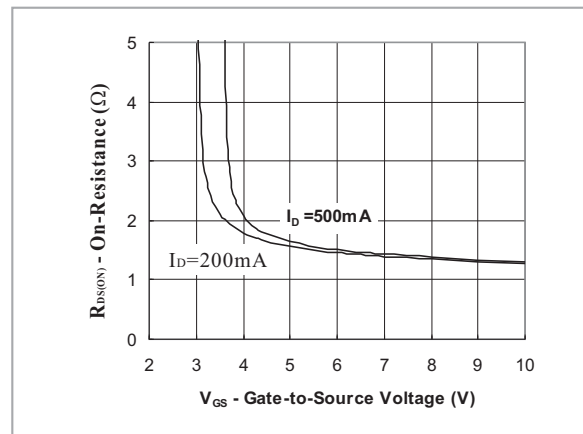


FIG.4- On Resistance vs Gate to Source Voltage

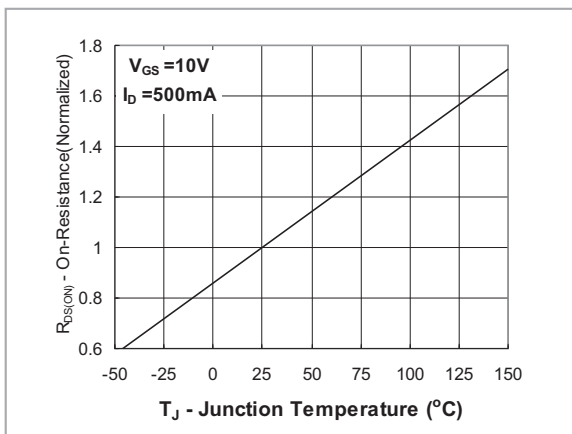


FIG.5- On Resistance vs Junction Temperature



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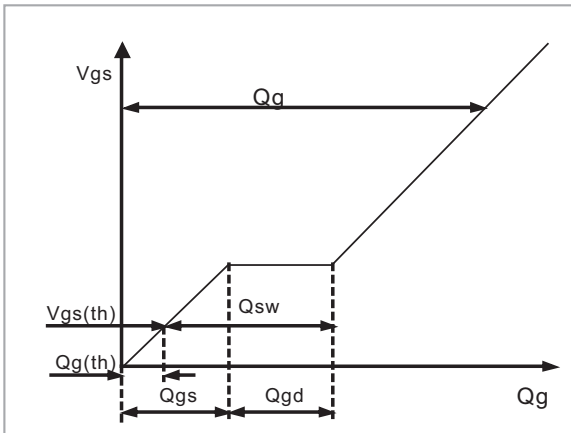


Fig.6 - Gate Charge Waveform

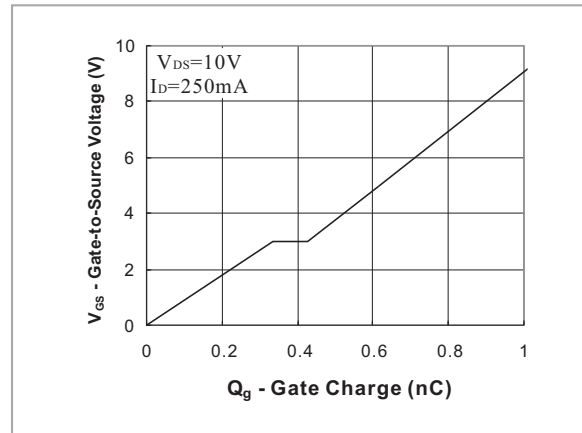


Fig.7 - Gate Charge

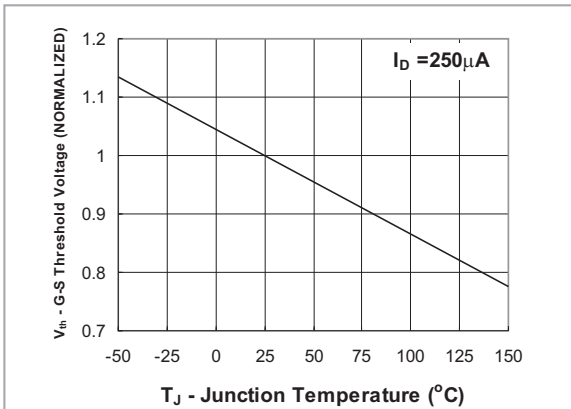


Fig.8 - Threshold Voltage vs Temperature

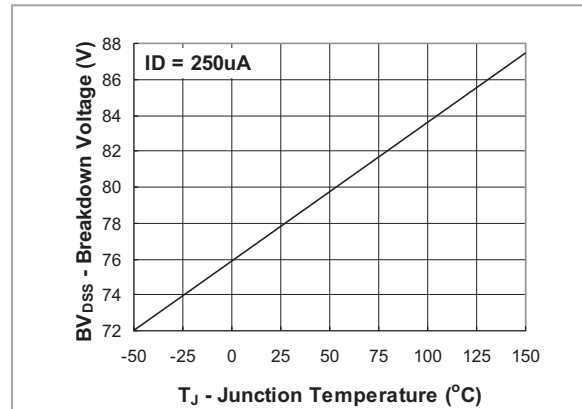


Fig.9 - Breakdown Voltage vs Junction Temperature

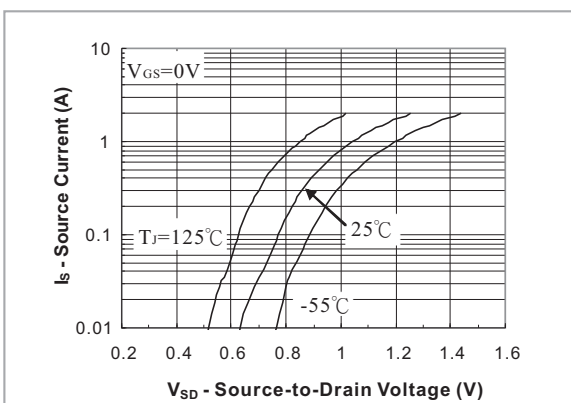
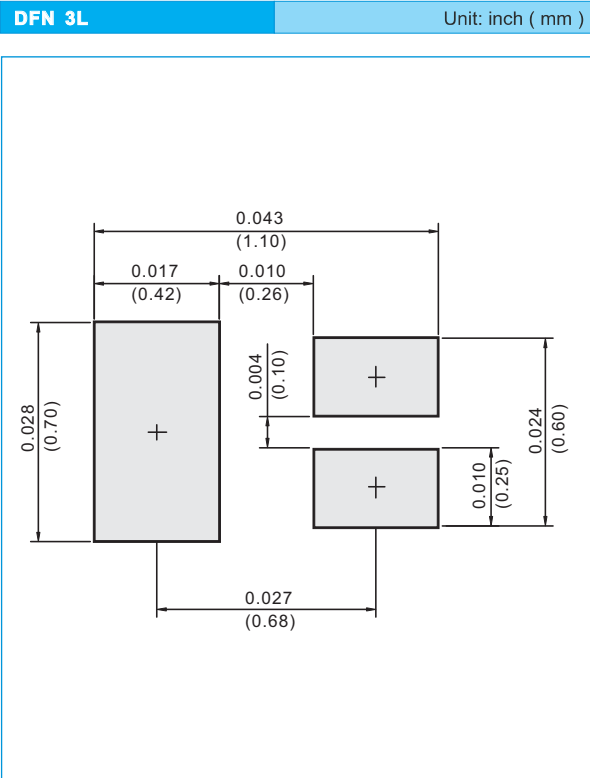


Fig.10 - Source-Drain Diode Forward Voltage



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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
T/R - 8K per 7" plastic Reel

LEGAL STATEMENT

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